NSN 5962-01-257-4585

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View Online at https://aerobasegroup.com/nsn/5962-01-257-4585

view Offilite at https://aerobasegroup.com/hist//3302-01-237-4303
Overall Width:
Between 0.745 inches and 1.040 inches
Body Length:
0.540 inches
Body Width:
Between 0.245 inches and 0.300 inches
Body Height:
Between 0.045 inches and 0.100 inches
Maximum Power Dissipation Rating:
2.0 watts
Operating Tempurature Range:
-55.0/+125.0 degrees celsius
Storage Tempurature Range:
-65.0/+150.0 degrees celsius
Features Provided:
Bipolar and programmable and monolithic
Inclosure Material:
Ceramic
Inclosure Configuration:
Flat pack
Output Logic Form:
Transistor-transistor logic
Input Circuit Pattern:
10 input
Case Outline Source And Designator:
F-9 mil-m-38510
Current Rating Per Characteristic:
100.00 milliamperes forward current, peak total value not applicable
Terminal Surface Treatment:
Solder
Voltage Rating And Type Per Characteristic:
-0.5 volts power source and 12.0 volts power source
Time Rating Per Chacteristic:
45.00 nanoseconds propagation delay time, low to high level output and 45.00 nanoseconds propagation delay time, high to low level
output
Memory Device Type:
Pal
Test Data Document:
96906-mil-std-883 standard (includes industry or association standards, individual manufactureer standards, etc.).

Shelf Life: N/a

20 flat leads

Terminal Type And Quantity:

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Demilitarization:

No

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